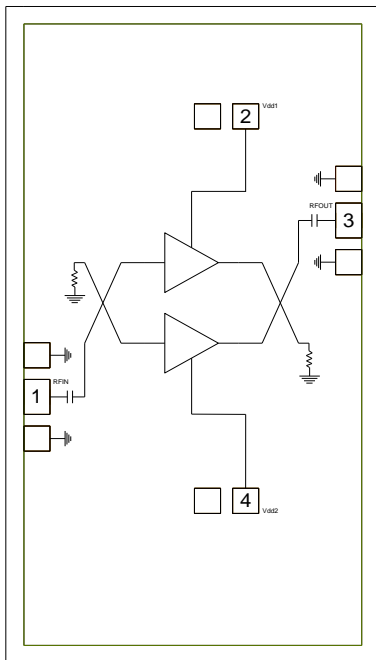


Product Overview

The CMD199 is a wideband GaAs MMIC driver amplifier ideally suited for military, space and communications systems where small size and high linearity are needed. At 30 GHz the device delivers 15 dB of gain with a corresponding output 1 dB compression point of +19.5 dBm and noise figure of 3.5 dB. The CMD199 is a 50 ohm matched design which eliminates the need for external DC blocks and RF port matching. The CMD199 offers full passivation for increased reliability and moisture protection.

Functional Block Diagram



Key Features

- Wide Bandwidth
- Positive Gain Slope
- Low Noise and High Linearity
- Excellent Return Losses
- Small Die Size: 1550 um x 2820 um

Ordering Information

Part No.	Description
CMD199	26-35 GHz Balanced Driver Amplifier, 100 Piece Gel Pack

Electrical Performance ($V_{dd1} = V_{dd2} = 5.0\text{ V}$, $T_A = 25\text{ }^\circ\text{C}$, $F = 30\text{ GHz}$)

Parameter	Min	Typ	Max	Units
Frequency Range		26 - 35		GHz
Gain		15		dB
Noise Figure		3.5		dB
Input Return Loss		14		dB
Output Return Loss		20		dB
Output P1dB		19.5		dBm
Supply Current ($I_{dd1} + I_{dd2}$)		72		mA

Absolute Maximum Ratings

Parameter	Rating
Drain Voltage, V_{dd1} , V_{dd2}	7.0 V
RF Input Power	+20 dBm
Channel Temperature, T_{ch}	150 °C
Power Dissipation, P_{diss}	883 mW
Thermal Resistance, θ_{JC}	73.6 °C/W
Operating Temperature	-55 to 85 °C
Storage Temperature	-55 to 150 °C

Exceeding any one or combination of the maximum ratings may cause permanent damage to the device.

Recommended Operating Conditions

Parameter	Min	Typ	Max	Units
V_{dd1} , V_{dd2}	3.0	5.0	7.0	V
I_{dd1}		36		mA
I_{dd2}		36		mA

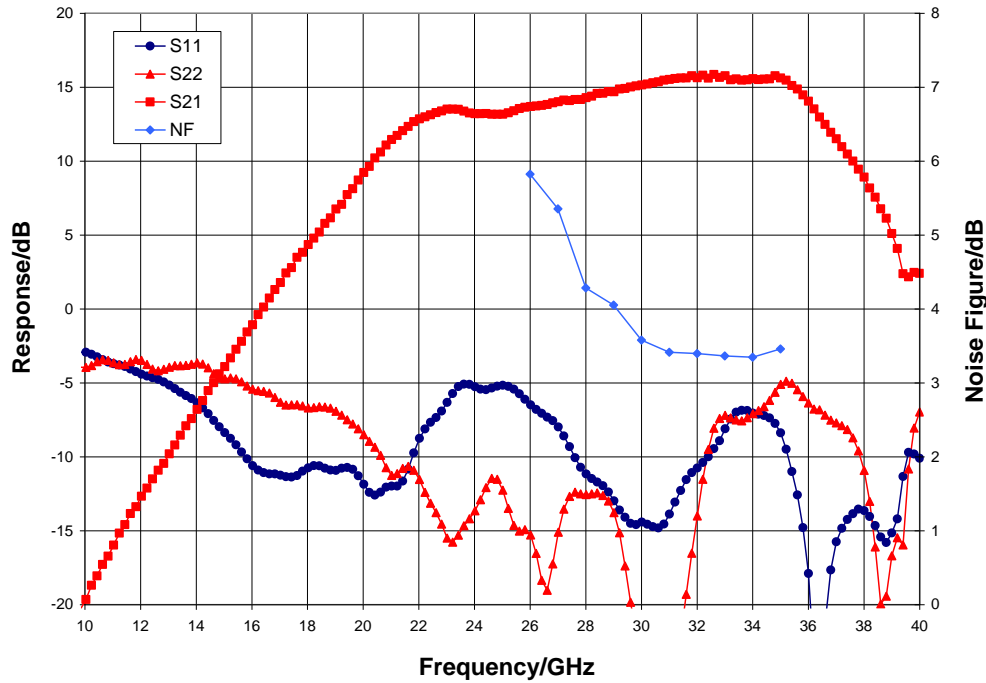
Electrical performance is measured at specific test conditions. Electrical specifications are not guaranteed over all recommended operating conditions.

Electrical Specifications ($V_{dd1} = V_{dd2} = 5.0$ V, $T_A = 25$ °C)

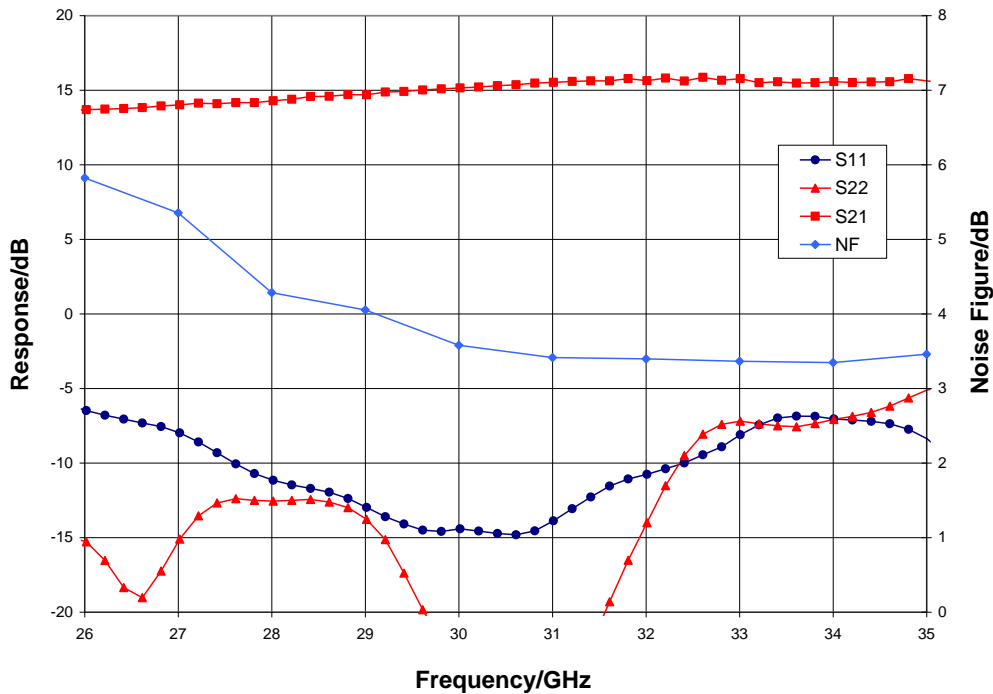
Parameter	Min		Typ		Max		Units
Frequency Range			26 - 30		30 - 35		GHz
Gain	11	14	18	12	15.5	18.5	dB
Noise Figure		4.5			3.5		dB
Input Return Loss		11			10		dB
Output Return Loss		13			8		dB
Output P1dB	16	19		14	19		dBm
Output IP3		24			24.5		dBm
Supply Current ($I_{dd1} + I_{dd2}$)	50	72	94	50	72	94	mA
Gain Temperature Coefficient		0.02			0.02		dB/°C
Noise Figure Temperature Coefficient		0.014			0.014		dB/°C

Typical Performance

Broadband Performance, $V_{dd1} = V_{dd2} = 5.0 \text{ V}$, $I_{dd1} = I_{dd2} = 36 \text{ mA}$, $T_A = 25 \text{ }^\circ\text{C}$

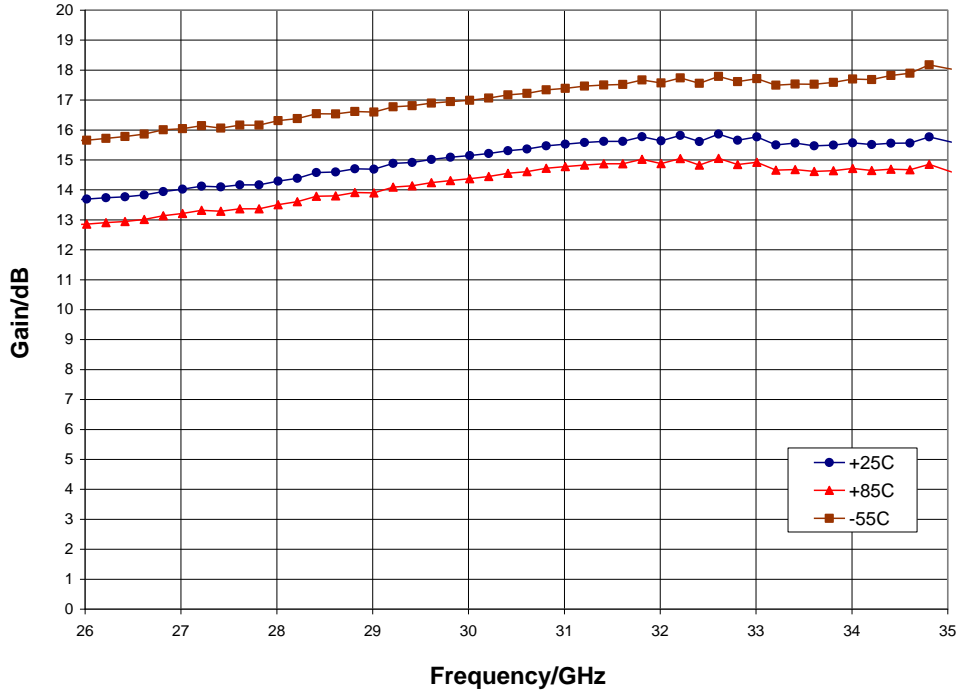


Narrow-band Performance, $V_{dd1} = V_{dd2} = 5.0 \text{ V}$, $I_{dd1} = I_{dd2} = 36 \text{ mA}$, $T_A = 25 \text{ }^\circ\text{C}$

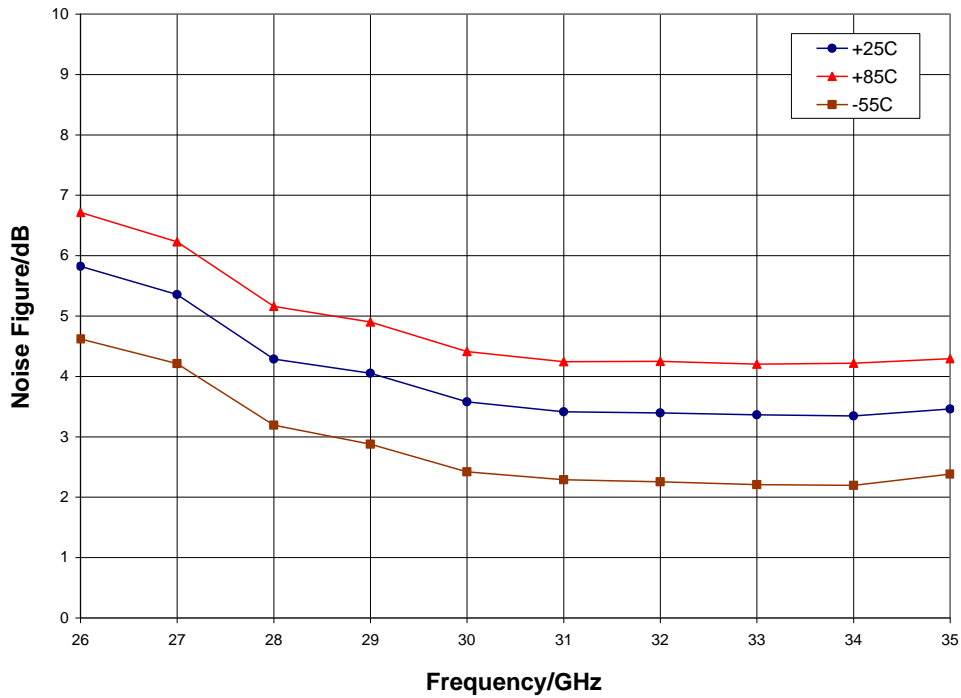


Typical Performance

Gain vs. Temperature, $V_{dd1} = V_{dd2} = 5.0\text{ V}$

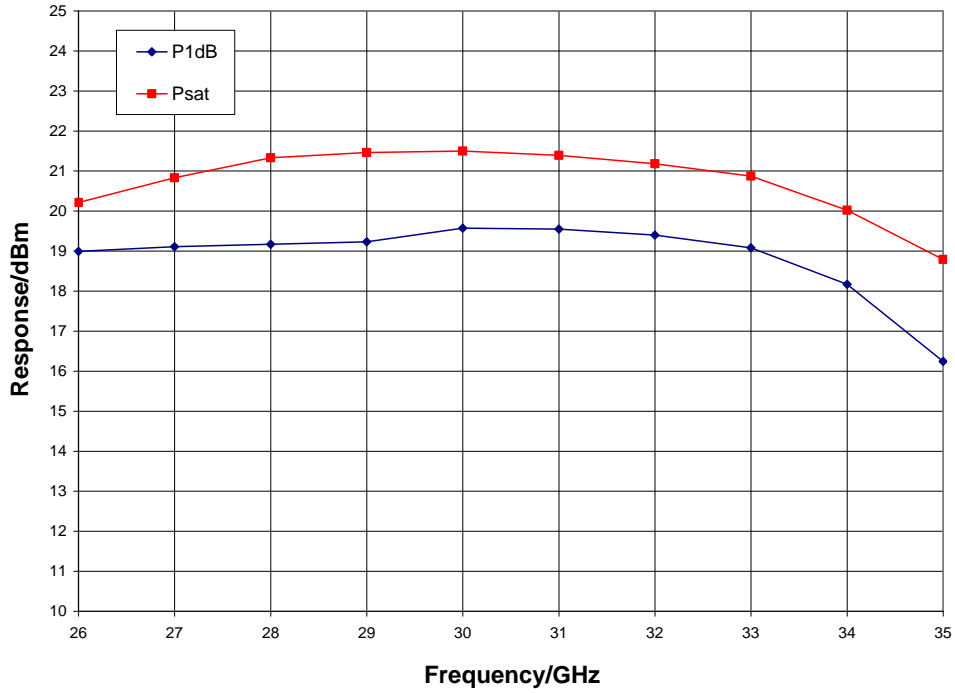


Noise Figure vs. Temperature, $V_{dd1} = V_{dd2} = 5.0\text{ V}$

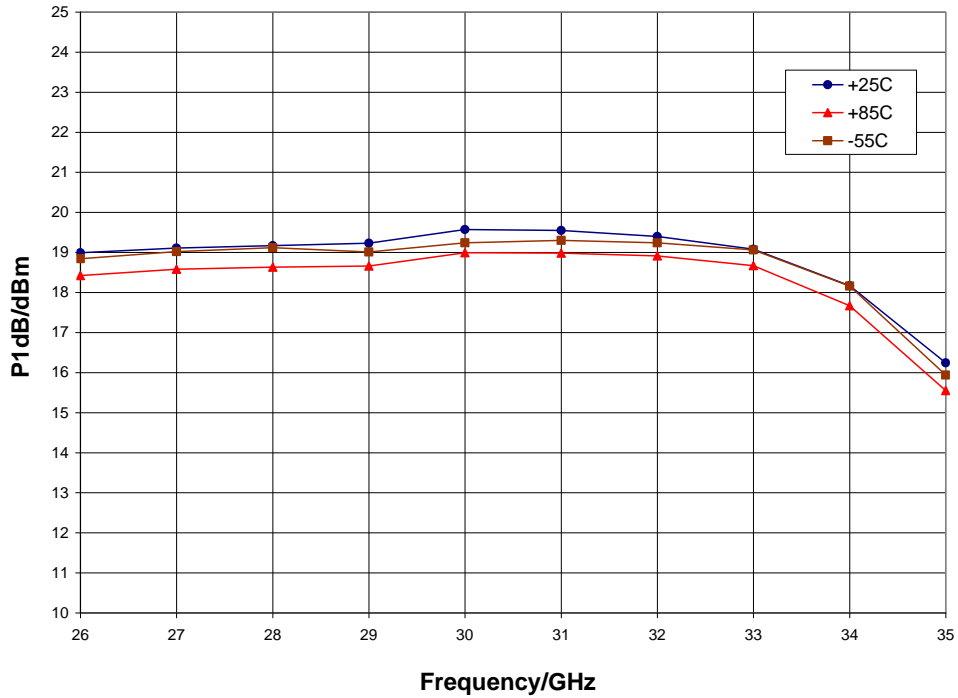


Typical Performance

Output Power, $V_{dd1} = V_{dd2} = 5.0\text{ V}$, $T_A = 25\text{ }^\circ\text{C}$

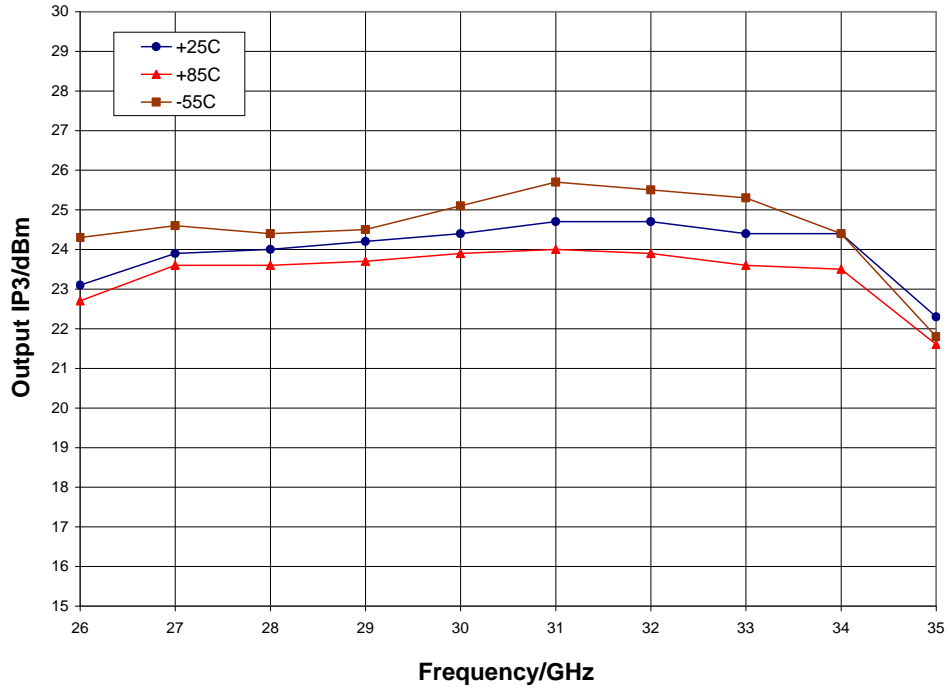


P1dB vs. Temperature, $V_{dd1} = V_{dd2} = 5.0\text{ V}$



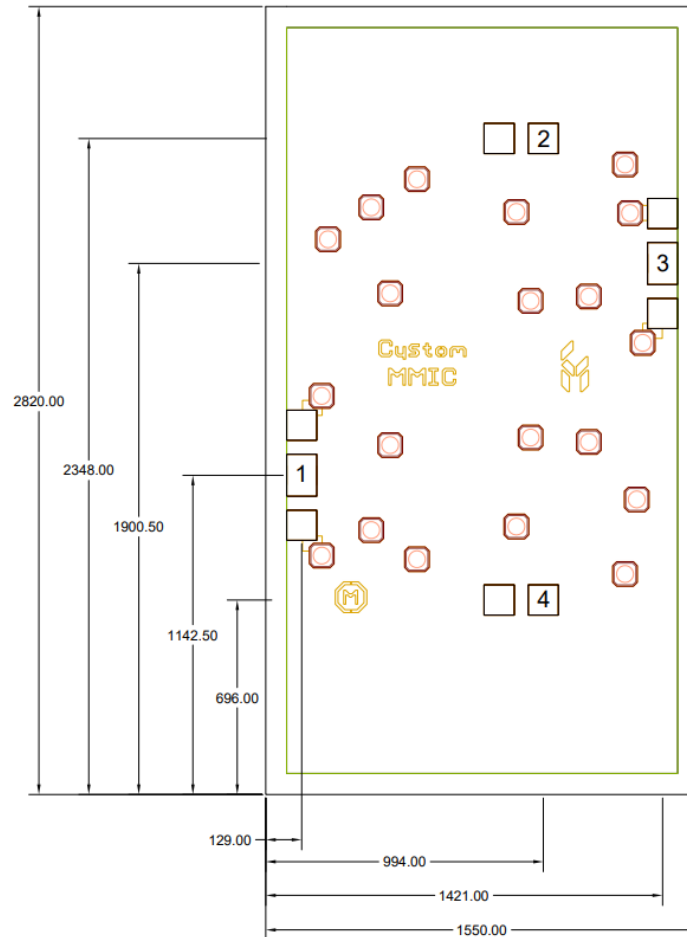
Typical Performance

Output IP3 vs. Temperature, $V_{dd1} = V_{dd2} = 5.0\text{ V}$



Mechanical Information

Die Outline (all dimensions in microns)

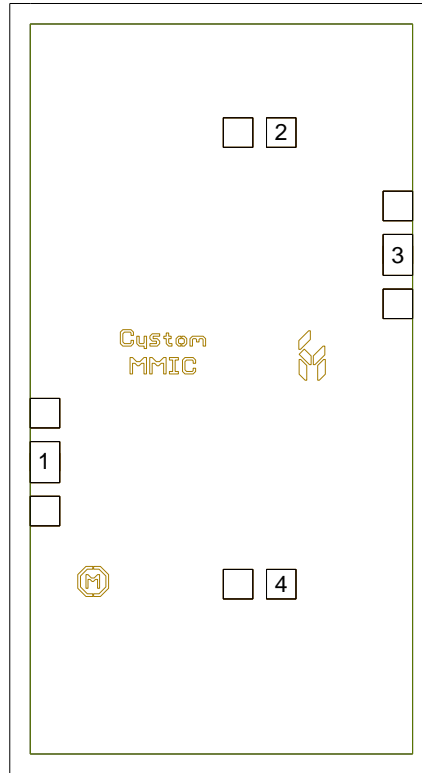


Notes:

1. No connection required for unlabeled pads
2. Backside is RF and DC ground
3. Backside and bond pad metal: Gold
4. Die is 85 microns thick
5. DC bond pads (2, 4) are 100 x 100 microns
6. RF bond pads (1, 3) are 100 x 150 microns

Pad Description

Pad Diagram



Functional Description

Pad	Function	Description	Schematic
1	RF in	DC blocked and 50 ohm matched	
2, 4	V _{dd1} , V _{dd2}	Power supply voltage Decoupling and bypass caps required	
3	RF out	DC blocked and 50 ohm matched	
Backside	Ground	Connect to RF / DC ground	

Applications Information

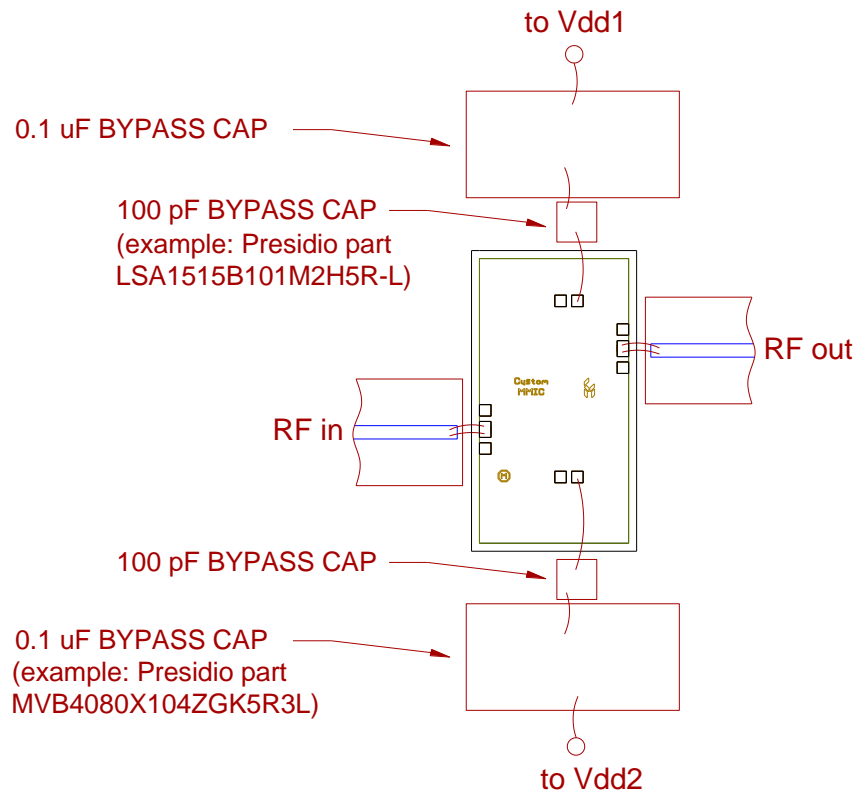
Assembly Guidelines

The backside of the CMD199 is RF ground. Die attach should be accomplished with electrically and thermally conductive epoxy only. Eutectic attach is not recommended. Standard assembly procedures should be followed for high frequency devices. The top surface of the semiconductor should be made planar to the adjacent RF transmission lines, and the RF decoupling capacitors placed in close proximity to the DC connections on chip.

RF connections should be made as short as possible to reduce the inductive effect of the bond wire. Use of a 0.8 mil thermosonic wedge bonding is highly recommended as the loop height will be minimized. The RF input and output require a double bond wire as shown.

The semiconductor is 85 um thick and should be handled by the sides of the die or with a custom collet. Do not make contact directly with the die surface as this will damage the monolithic circuitry. Handle with care.

Assembly Diagram



GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.

Applications Information

Biasing and Operation

The CMD199 is biased with a positive drain supply. Performance is optimized when the drain voltage is set to +5.0 V.

Turn ON procedure:

1. Apply drain voltage V_{dd1} , V_{dd2} and set to +5 V

Turn OFF procedure:

1. Turn off drain voltage V_{dd1} , V_{dd2}

RF power can be applied at any time.

Handling Precautions

Parameter	Rating	Standard
ESD – Human Body Model (HBM)	Class 1A	ESDA / JEDEC JS-001-2012



Caution!
 ESD-Sensitive Device

RoHS Compliance

This part is compliant with 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment) as amended by Directive 2015/863/EU.

This product also has the following attributes:

- Lead Free
- Antimony Free
- TBBP-A (C₁₅H₁₂Br₄O₂) Free
- SVHC Free
- Halogen Free
- PFOS Free

Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations:

Web: www.qorvo.com

Tel: 1-844-890-8163

Email: customer.support@qorvo.com

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